

INFINEON HALF BRIDGE MODULE(FF11MR12W1M1_B11) 1200V CoolSiC™ MOSFET ANALYSIS REPORT

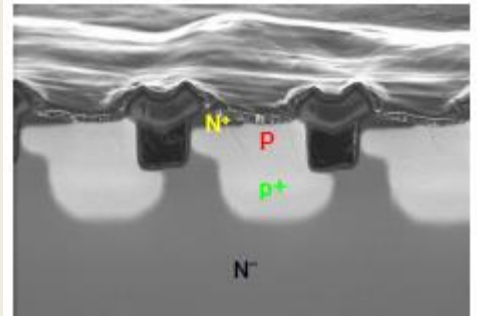
Sep 2017. LTEC Corporation released a detailed structure and process analysis report of 1200V 1200V CoolSiC™ MOSFET device. This device is the 1st product from Infineon using unique asymmetric trench gate transistor. This device has low Ron comparable with other device makers such as Rohm, Wolfspeed.



Module



SiC die



SEM cross section

Device features

- Max. operating voltage: 1200V, rated DC Drain current I_D @25°C = 100A
- Very low specific On-resistance, $R_{ON} \times A = 36\text{m}\Omega \times \text{mm}^2$

The report has two individually purchasable sections: a Structure Analysis(80pages) and a Process Analysis section(29pages). The Structure Analysis section reveals the physical construction of the device, including EDX materials analysis, and many other fine details. The Process Analysis section includes manufacturing process flow, the estimated number of photomasking steps, and the impurity concentration of the epitaxial layer.

Structure analysis report:

\$5,000

Process analysis report:

\$4,000

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